

## THE SPECIFICATION OF AlGaAs IR LED CHIP "I26N-84"

### 1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 880 nm (Typ.).

### 2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25 deg.C)

CONDITION	Symbol	Condition	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V <sub>f</sub>	IF=20mA		1.42		V
Reverse Voltage	V <sub>r</sub>	IR=10uA	5			V
Radiated Power <sup>1)</sup>	P <sub>o</sub>	IF=20mA	4.0			mW
Peak Wavelength	λ	IF=20mA	875	880	892	nm
Spectral Radiation Bandwidth		IF=20mA		55		nm
Rise Time	T <sub>r</sub>	IF <sub>p</sub> =100mA T <sub>w</sub> =125ns,Duty=25%		20		ns
Fall Time	T <sub>f</sub>	IF <sub>p</sub> =100mA T <sub>w</sub> =125ns,Duty=25%		20		ns
PeakForward Voltage	V <sub>fm</sub>	IF <sub>p</sub> =200mA T <sub>w</sub> =10us,Duty=10%		2.05		V

1) LED chip is mounted on TO-18 gold header without resin coated.

### 3. ABSOLUTE MAXIMUM RATINGS

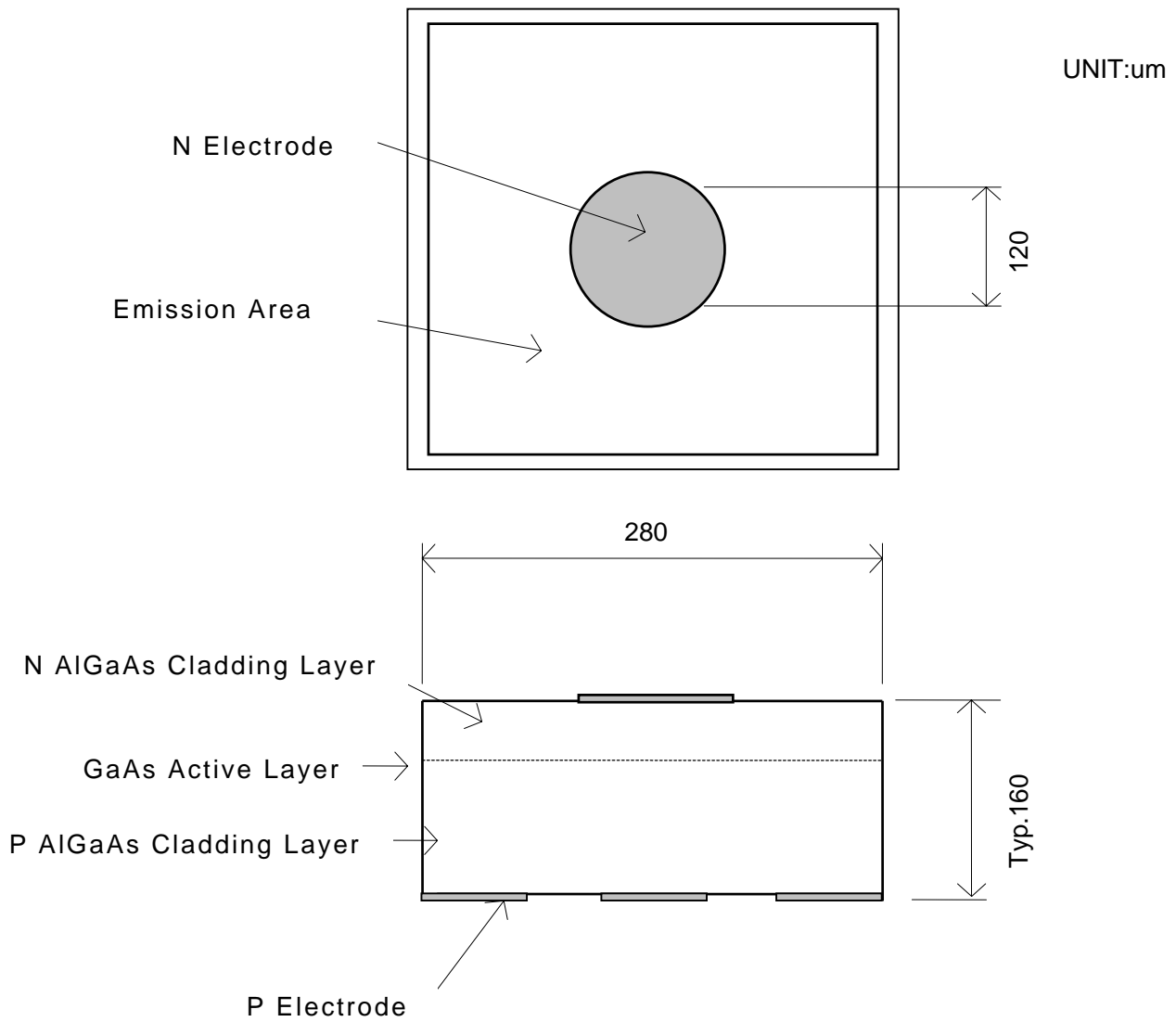
Continuous Maximum Forward Current : 80 mA(DC)  
 Reverse Voltage : 5 V(IR=10uA)  
 Storage Temperature  
   while on mylar membrane : 0 to 40 deg. C  
   after removal from mylar membrane : -40 to 100 deg. C

### 4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material : AlGaAs  
 2)Structure : Double Hetero Structure  
 3)Junction Size : 0.280mmX0.280mm  
 4)Thickness : 0.160mm  
 5)Bond Pad Size : 0.120mm diameter  
 6)Anode Metallization : Gold Alloy  
 7)Cathode Metallization: Gold Alloy

Physical Dimensions

Model I26N-84



Remark: This specification is for reference purpose only, and subject to change without prior notice.  
Approved specification shall be obtained for the regular purchase.